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# Power Matters<sup>™</sup>

Home > 2N7376 (#23646)

Microsemi.

### 2N7376 (#23646)

## Products

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### Overview Diagrams

Electrical Rating Symbol Min Typ Max Un Collector to Emitter Saturation Voltage V <sub>CE(Sat)</sub> 0.40 V						
Collector to Emitter Saturation Voltage V <sub>CE(sat)</sub> 0.40 V	Electrical Rating	Symbol	Min	Тур	Max	Unit
	Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>			0.40	V
DC Current Gain         HFE         40.00         120.00	DC Current Gain	HFE	40.00		120.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V <sub>BR(CBO)</sub>			250.00	V
Collector Current (dc)	I <sub>C</sub>			5.00	А
Collector-Emitter Voltage (Base Open)	V <sub>CEO</sub>			200.00	V
Emitter-Base Voltage (Collector Open)	V <sub>EBO</sub>			6.00	V
Power Dissipation, Total	P <sub>T</sub>			58.00	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT( BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices Transistors BJT( BiPolar Junction Transistor) NPN Transistor

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